



60V N-Channel Enhancement Mode MOSFET

Voltage

60 V

Current

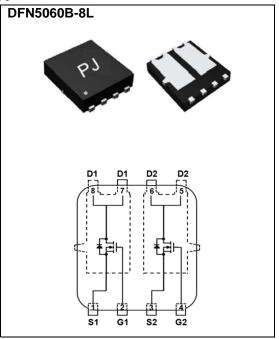
40 A

Features

- $R_{DS(ON)}$, $V_{GS}@10V$, $I_D@20A<17m\Omega$
- R_{DS(ON)}, V_{GS}@4.5V, I_D@10A<20mΩ
- High switching speed
- Improved dv/dt capability
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case: DFN5060B-8L Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.0035 ounces, 0.092 grams



Maximum Ratings and Thermal Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V _{DS}	60	\/	
Gate-Source Voltage		V_{GS}	<u>+</u> 20	V	
Continuous Drain Current	T _C =25°C	- I _D	40	A	
	T _C =100°C		25		
Pulsed Drain Current (Note 1)	T _C =25°C	I _{DM}	160		
Power Dissipation	T _C =25°C	Po	56	W	
	T _C =100°C		22		
Continuous Drain Current	T _A =25°C	I _D	7.0	А	
	T _A =70°C		5.5		
Power Dissipation	T _A =25°C	Po	1.7	W	
	T _A =70°C		1.1		
Single Pulse Avalanche Energy ^(Note 6)		E _{AS}	45	mJ	
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~150	°C	
Typical Thermal Resistance (Note 4,5)	Junction to Case	$R_{ heta JC}$	2.2	°C/W	
	Junction to Ambient	$R_{\theta JA}$	73.5		

Limited only By Maximum Junction Temperature





Electrical Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V,I _D =250uA	60	-	-	V	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250uA$	1.0	1.7	2.5		
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V,I _D =20A	-	13	17	mΩ	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =4.5V,I _D =10A	-	16	20	mΩ	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V,V _{GS} =0V	-	-	1.0	uA	
Gate-Source Leakage Current	I_{GSS}	V _{GS} = <u>+</u> 20V,V _{DS} =0V	-	-	<u>+</u> 100	nA	
Dynamic (Note 7)							
Total Gate Charge	Q_{g}	V _{DS} =30V, I _D =10A, V _{GS} =4.5V (Note 1,2)	-	13.5	-	nC	
Gate-Source Charge	Q_gs		-	4.8	-		
Gate-Drain Charge	Q_{gd}		-	4.9	-		
Input Capacitance	Ciss	V _{DS} =25V, V _{GS} =0V,	-	1574	-	pF	
Output Capacitance	Coss		-	118	-		
Reverse Transfer Capacitance	Crss	f=1.0MHZ	-	77	-		
Turn-On Delay Time	td _(on)	\/ AF\/ AA	-	11	-		
Turn-On Rise Time	t _r	V_{DD} =15V, I_{D} =1A, V_{GS} =10V, R_{G} =6 Ω (Note 1,2)	-	11	-	ns	
Turn-Off Delay Time	td _(off)		-	35	-		
Turn-Off Fall Time	t _f	, , ,	-	8.1	-		
Drain-Source Diode							
Maximum Continuous Drain-Source			-	-	40	А	
Diode Forward Current	I _S						
Diode Forward Voltage	V_{SD}	I _S =1A,V _{GS} =0V	-	0.68	1	V	

NOTES:

- 1. Pulse width<a>300us, Duty cycle<a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited.
- 5. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. The test condition is L=0.1mH, I_{AS}=30A, V_{DD}=25V, V_{GS}=10V, Starting T_J=25°C
- 7. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

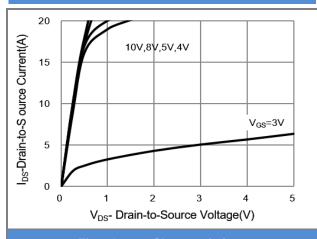


Fig.1 Output Characteristics

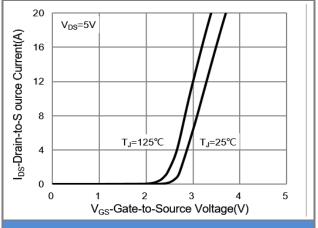


Fig.2 Transfer Characteristics

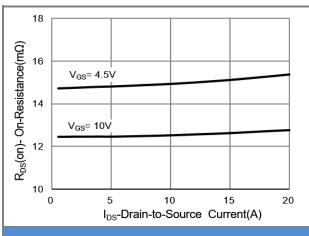


Fig.3 On-Resistance vs. Drain Current

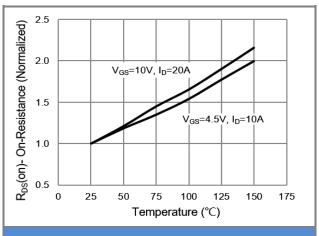
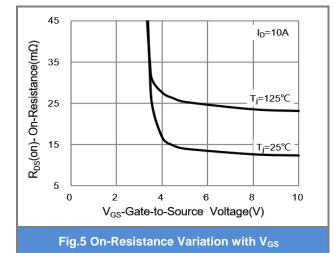


Fig.4 On-Resistance vs. Junction temperature



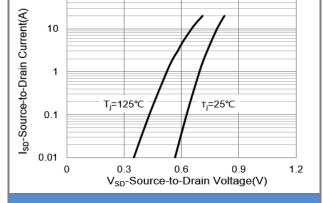


Fig.6 Source-Drain Diode Forward Voltage

100





TYPICAL CHARACTERISTIC CURVES

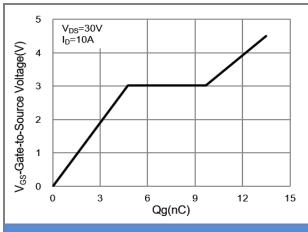
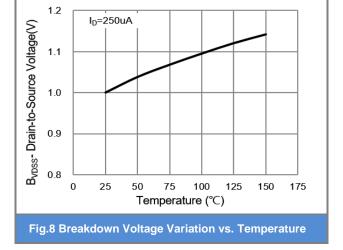


Fig.7 Gate-Charge Characteristics



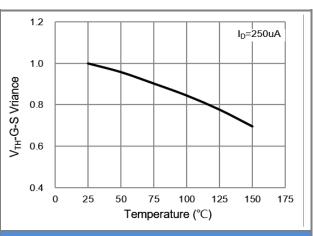


Fig.9 Threshold Voltage Variation with Temperature

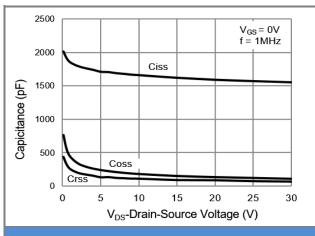


Fig.10 Capacitance vs. Drain-Source Voltage

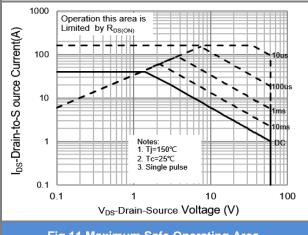


Fig.11 Maximum Safe Operating Area





TYPICAL CHARACTERISTIC CURVES

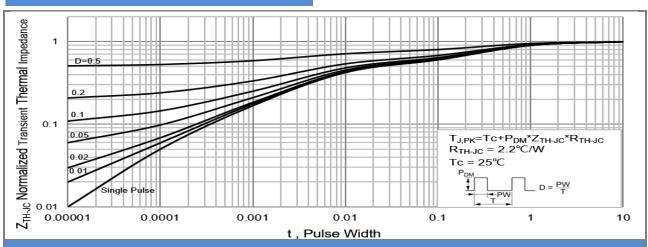


Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width

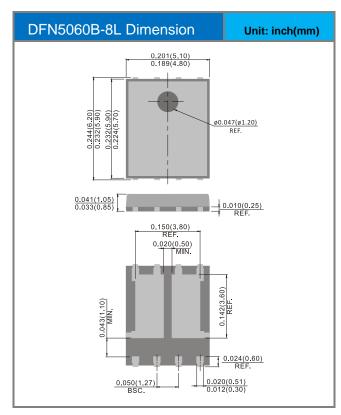


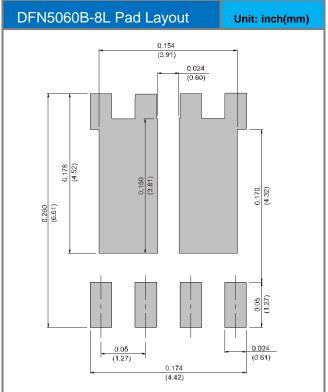


Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type	Marking	Version	
PJQ5866A_R2_00001	DFN5060B-8L	3000pcs / 13" reel	Q5866A	Halogen free	

Packaging Information & Mounting Pad Layout





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